ABSTRACT

The invention concerns a method for forming a semi-conducting structure, comprising:

a) the formation of at least one part of a circuit, in or on the superficial layer (2) of a substrate, comprising said superficial layer (2), a buried layer (4) underneath the superficial layer, and an underlying layer (6) serving as first support,

b) a transfer of this substrate onto a handle substrate (20) then an elimination of the first support (6),

c) the formation of an electrically conducting or ground plane forming layer (14) on the buried layer (4),

d) the formation, on this electrically conducting or ground plane forming layer (14), of a bonding layer (12),

e) a transfer of the structure thus obtained onto a second support (30) and an elimination of the handle substrate (20).

Figure 2.